SiT8925B

High Frequency, Automotive AEC-Q100 Oscillator

Features

- AEC-Q100 with extended temperature range (-55°C to 125°C)
- Frequencies between 115.2 MHz and 137 MHz accurate to 6 decimal points
- 100% pin-to-pin drop-in replacement to quartz-based XO
- Excellent total frequency stability as low as ±20 ppm
- Industry best G-sensitivity of 0.1 PPB/G
- Low power consumption of 3.8 mA typical at 1.8V
- LVCMOS/LVTTL compatible output
- Industry-standard packages: 2.0 x 1.6, 2.5 x 2.0, 3.2 x 2.5, 5.0 x 3.2, 7.0 x 5.0 mm x mm
- RoHS and REACH compliant, Pb-free, Halogen-free and Antimony-free

Applications

- Automotive, extreme temperature and other high-rel electronics
- Infotainment systems, collision detection devices, and in-vehicle networking
- Powertrain control



Electrical Characteristics

Table 1. Electrical Characteristics

All Min and Max limits are specified over temperature and rated operating voltage with 15 pF output load unless otherwise stated. Typical values are at 25°C and nominal supply voltage.

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Frequency Range						
Output Frequency Range	f	115.20	–	137	MHz	Refer to Tables 13 to 15 for the exact list of supported frequencies
Frequency Stability and Aging						
Frequency Stability	F_stab	-20	–	+20	ppm	Inclusive of Initial tolerance at 25°C, 1st year aging at 25°C, and variations over operating temperature, rated power supply voltage and load (15 pF ± 10%).
		-25	–	+25	ppm	
		-30	–	+30	ppm	
		-50	–	+50	ppm	
Operating Temperature Range						
Operating Temperature Range (ambient)	T_use	-40	–	+85	°C	AEC-Q100 Grade 3
		-40	–	+105	°C	AEC-Q100 Grade 2
		-40	–	+125	°C	AEC-Q100 Grade 1
		-55	–	+125	°C	Extended cold, AEC-Q100 Grade1
Supply Voltage and Current Consumption						
Supply Voltage	Vdd	1.62	1.8	1.98	V	All voltages between 2.25V and 3.63V including 2.5V, 2.8V, 3.0V and 3.3V are supported. Contact SiTime for 1.5V support
		2.25	–	3.63	V	
Current Consumption	Idd	–	6	8	mA	No load condition, f = 125 MHz, Vdd = 2.25V to 3.63V
		–	4.9	6	mA	No load condition, f = 125 MHz, Vdd = 1.62V to 1.98V
LVCMOS Output Characteristics						
Duty Cycle	DC	45	–	55	%	
Rise/Fall Time	Tr, Tf	–	1.5	3	ns	Vdd = 2.25V - 3.63V, 20% - 80%
		–	1.5	2.5	ns	Vdd = 1.8V, 20% - 80%
Output High Voltage	VOH	90%	–	–	Vdd	IOH = -4 mA (Vdd = 3.0V or 3.3V) IOH = -3 mA (Vdd = 2.8V and Vdd = 2.5V) IOH = -2 mA (Vdd = 1.8V)
Output Low Voltage	VOL	–	–	10%	Vdd	IOL = 4 mA (Vdd = 3.0V or 3.3V) IOL = 3 mA (Vdd = 2.8V and Vdd = 2.5V) IOL = 2 mA (Vdd = 1.8V)
Input Characteristics						
Input High Voltage	VIH	70%	–	–	Vdd	Pin 1, OE
Input Low Voltage	VIL	–	–	30%	Vdd	Pin 1, OE
Input Pull-up Impedance	Z_in	–	100	–	kΩ	Pin 1, OE logic high or logic low
Startup and Resume Timing						
Startup Time	T_start	–	–	5.5	ms	Measured from the time Vdd reaches its rated minimum value
Enable/Disable Time	T_oe	–	–	130	ns	f = 115.20 MHz. For other frequencies, T_oe = 100 ns + 3 * cycles
Standby Current	I_std	–	2.6	–	µA	Vdd = 2.8V to 3.3V, $\overline{ST}$ = Low, Output is weakly pulled down
		–	1.4	–	µA	Vdd = 2.5V, $\overline{ST}$ = Low, Output is weakly pulled down
		–	0.6	–	µA	Vdd = 1.8V, $\overline{ST}$ = Low, Output is weakly pulled down

Table 1. Electrical Characteristics (continued)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
			Jitter			
RMS Period Jitter	T_jitt	–	1.6	2.5	ps	f = 125 MHz, 2.25V to 3.63V
		–	1.8	3	ps	f = 125 MHz, 1.8V
Peak-to-peak Period Jitter	T_pk	–	12	20	ps	f = 125 MHz, Vdd = 2.5V, 2.8V, 3.0V or 3.3V
		–	14	30	ps	f = 125 MHz, Vdd = 1.8V
RMS Phase Jitter (random)	T_phj	–	0.7	–	ps	f = 125 MHz, Integration bandwidth = 900 kHz to 7.5 MHz
		–	1.5	–	ps	f = 125 MHz, Integration bandwidth = 12 kHz to 20 MHz

Table 2. Pin Description

Pin	Symbol		Functionality
1	OE/NC	Output Enable	H[1]: specified frequency output L: output is high impedance. Only output driver is disabled.
		No Connect	Any voltage between 0 and Vdd or Open[1]: Specified frequency output. Pin 1 has no function.
2	GND	Power	Electrical ground[2]
3	OUT	Output	Oscillator output
4	VDD	Power	Power supply voltage[2]

Top View

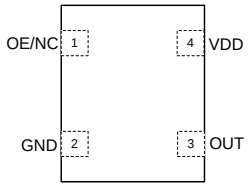


Figure 1. Pin Assignments

Notes:

1. In OE mode, a pull-up resistor of 10kΩ or less is recommended if pin 1 is not externally driven. If pin 1 needs to be left floating, use the NC option.
2. A capacitor of value 0.1 µF or higher between Vdd and GND is required.

Table 3. Absolute Maximum Limits

Attempted operation outside the absolute maximum ratings may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Storage Temperature	-65	150	°C
Vdd	-0.5	4	V
Electrostatic Discharge	–	2000	V
Soldering Temperature (follow standard Pb free soldering guidelines)	–	260	°C
Junction Temperature[3]	–	150	°C

Note:

3. Exceeding this temperature for extended period of time may damage the device.

Table 4. Thermal Consideration[4]

Package	θJA, 4 Layer Board (°C/W)	θJA, 2 Layer Board (°C/W)	θJC, Bottom (°C/W)
7050	142	273	30
5032	97	199	24
3225	109	212	27
2520	117	222	26
2016	152	252	36

Note:

4. Refer to JESD51 for θJA and θJC definitions, and reference layout used to determine the θJA and θJC values in the above table.

Table 5. Maximum Operating Junction Temperature[5]

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature
85°C	93°C
105°C	113°C
125°C	133°C

Note:

5. Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.

Table 6. Environmental Compliance

Parameter	Condition/Test Method
Mechanical Shock	**MIL-STD-883F, Method 2002**
Mechanical Vibration	**MIL-STD-883F, Method 2007**
Temperature Cycle	**JESD22, Method A104**
Solderability	**MIL-STD-883F, Method 2003**
Moisture Sensitivity Level	**MSL1 @ 260°C**

Test Circuit and Waveform

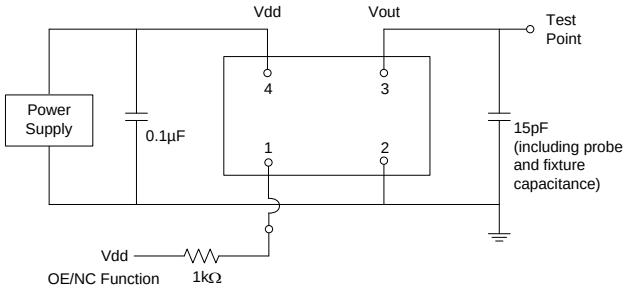


Figure 2. Test Circuit[6]

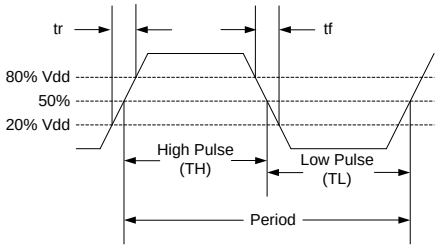
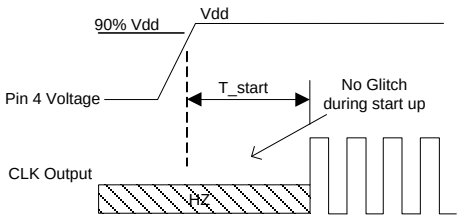


Figure 3. Waveform

Note:

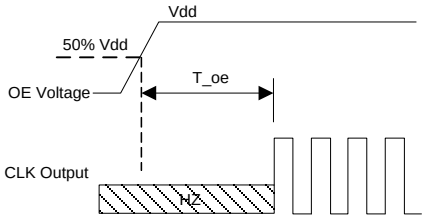
6. Duty Cycle is computed as Duty Cycle = TH/Period.

Timing Diagrams



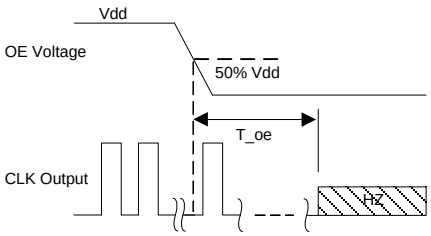
T_start: Time to start from power-off

Figure 4. Startup Timing (OE Mode)[7]



T_oe: Time to re-enable the clock output

Figure 5. OE Enable Timing (OE Mode Only)



T_oe: Time to put the output in High Z mode

Figure 6. OE Disable Timing (OE Mode Only)

Note:

7. SiT8925 has “no runt” pulses and “no glitch” output during startup or resume.

Performance Plots[8]

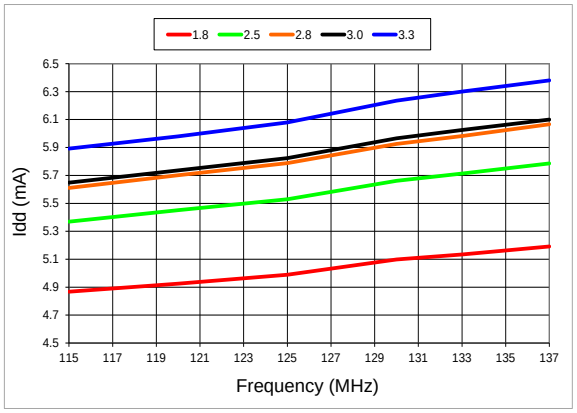


Figure 7. Idd vs Frequency

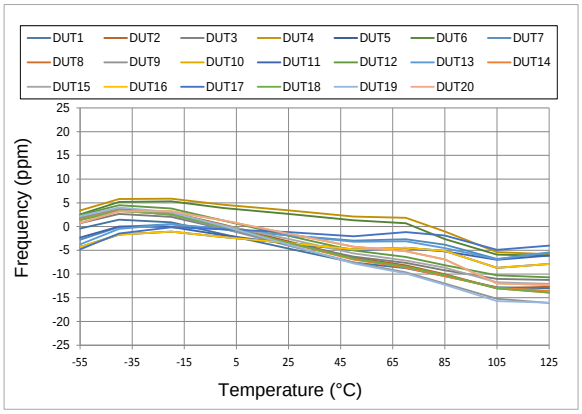


Figure 8. Frequency vs Temperature

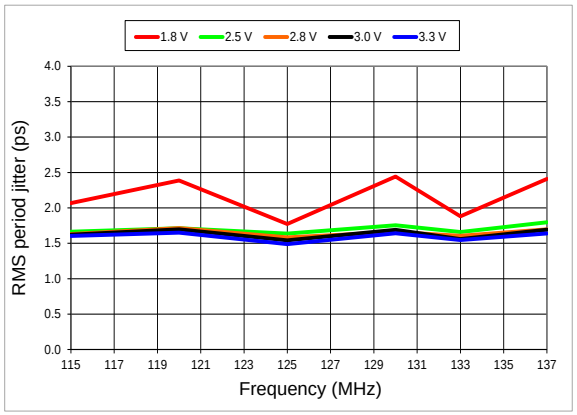


Figure 9. RMS Period Jitter vs Frequency

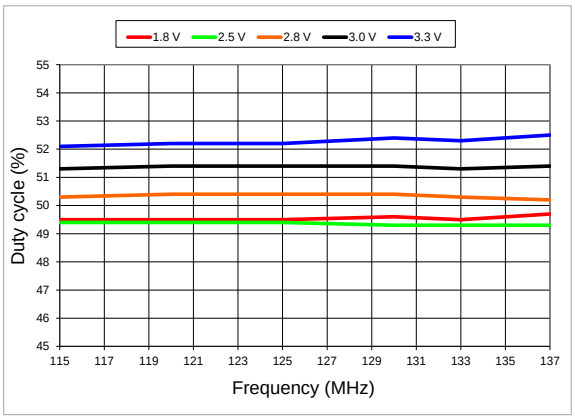


Figure 10. Duty Cycle vs Frequency

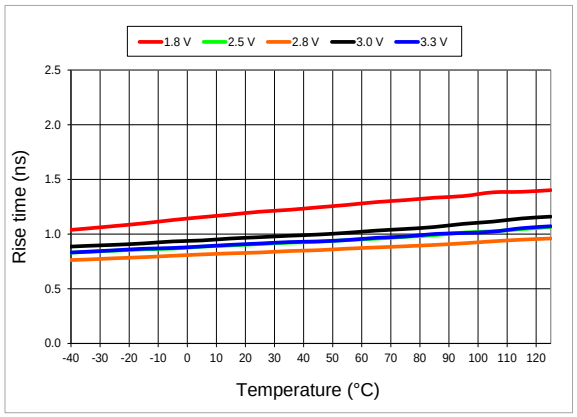


Figure 11. 20%-80% Rise Time vs Temperature

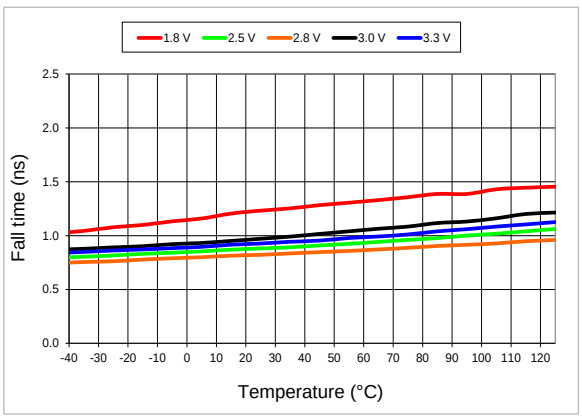


Figure 12. 20%-80% Fall Time vs Temperature

Performance Plots[8]

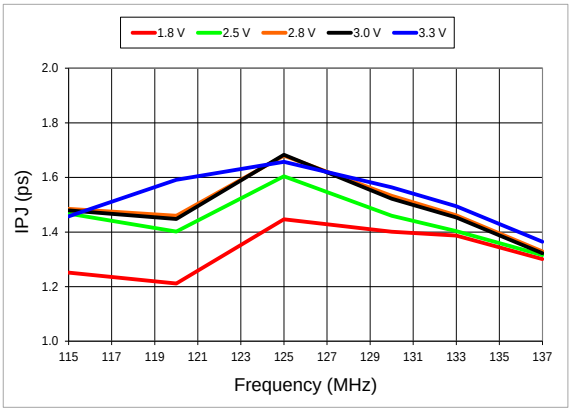


Figure 13. RMS Integrated Phase Jitter Random (12 kHz to 20 MHz) vs Frequency[9]

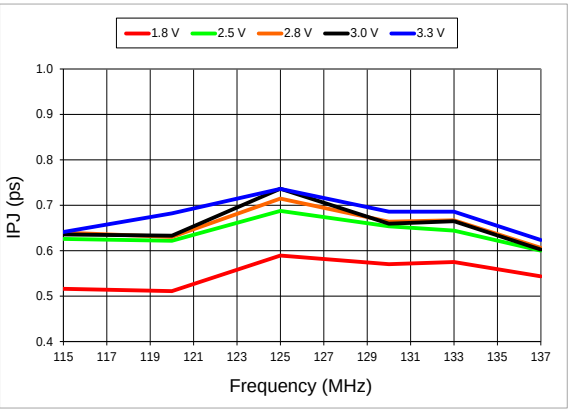


Figure 14. RMS Integrated Phase Jitter Random (900 kHz to 20 MHz) vs Frequency[9]

Notes:

8. All plots are measured with 15 pF load at room temperature, unless otherwise stated.
9. Phase noise plots are measured with Agilent E5052B signal source analyzer.

Programmable Drive Strength

The SiT8925 includes a programmable drive strength feature to provide a simple, flexible tool to optimize the clock rise/fall time for specific applications. Benefits from the programmable drive strength feature are:

- Improves system radiated electromagnetic interference (EMI) by slowing down the clock rise/fall time.
- Improves the downstream clock receiver's (RX) jitter by decreasing (speeding up) the clock rise/fall time.
- Ability to drive large capacitive loads while maintaining full swing with sharp edge rates.

For more detailed information about rise/fall time control and drive strength selection, see the SiTime Application Notes section.

EMI Reduction by Slowing Rise/Fall Time

Figure 15 shows the harmonic power reduction as the rise/fall times are increased (slowed down). The rise/fall times are expressed as a ratio of the clock period. For the ratio of 0.05, the signal is very close to a square wave. For the ratio of 0.45, the rise/fall times are very close to near-triangular waveform. These results, for example, show that the 11th clock harmonic can be reduced by 35 dB if the rise/fall edge is increased from 5% of the period to 45% of the period.

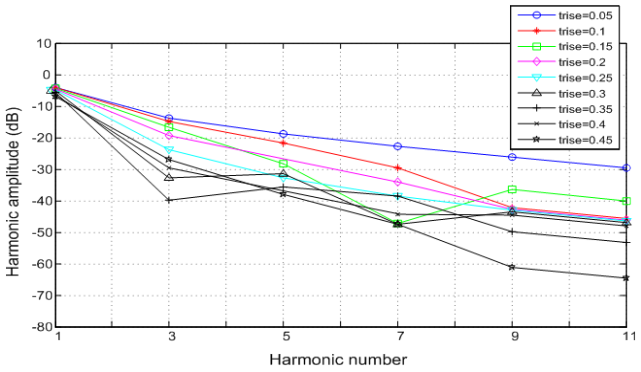


Figure 15. Harmonic EMI reduction as a Function of Slower Rise/Fall Time

Jitter Reduction with Faster Rise/Fall Time

Power supply noise can be a source of jitter for the downstream chipset. One way to reduce this jitter is to speed up the rise/fall time of the input clock. Some chipsets may also require faster rise/fall time in order to reduce their sensitivity to this type of jitter. Refer to the Rise/Fall Time Tables (Table 7 to Table 11) to determine the proper drive strength.

High Output Load Capability

The rise/fall time of the input clock varies as a function of the actual capacitive load the clock drives. At any given drive strength, the rise/fall time becomes slower as the output load increases. As an example, for a 3.3V SiT8925 device with default drive strength setting, the typical rise/fall time is 0.46 ns for 5 pF output load. The typical rise/fall time slows down to 1 ns when the output load increases to 15 pF. One can choose to speed up the rise/fall time to 0.72 ns by then increasing the driven strength setting on the SiT8925 to "F".

The SiT8925 can support up to 30 pF in maximum capacitive loads with up to 3 additional drive strength settings. Refer to the Rise/Tall Time Tables (Table 7 to 11) to determine the proper drive strength for the desired combination of output load vs. rise/fall time.

SiT8925 Drive Strength Selection

Tables 7 through 11 define the rise/fall time for a given capacitive load and supply voltage.

1. Select the table that matches the SiT8925 nominal supply voltage (1.8V, 2.5V, 2.8V, 3.0V, 3.3V)
2. Select the capacitive load column that matches the application requirement (5 pF to 30 pF)
3. Under the capacitive load column, select the desired rise/fall times.
4. The left-most column represents the part number code for the corresponding drive strength.
5. Add the drive strength code to the part number for ordering purposes.

Calculating Maximum Frequency

Based on the rise and fall time data given in Tables 7 through 11, the maximum frequency the oscillator can operate with guaranteed full swing of the output voltage over temperature as follows:

$$\text{Max Frequency} = \frac{1}{5 \times \text{Trf_20/80}}$$

where Trf_20/80 is the typical value for 20%-80% rise/fall time.

Example 1

Calculate f_{MAX} for the following condition:

- Vdd = 3.3V (Table 11)
- Capacitive Load: 30 pF
- Desired Tr/f time = 1.46 ns
  (rise/fall time part number code = U)

Part number for the above example:

SiT8925BA**E**12-18E-137.000000

Drive strength code is inserted here. Default setting is "-"

Rise/Fall Time (20% to 80%) vs C_{LOAD} Tables

Table 7. Vdd = 1.8V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)		
Drive Strength\ C_{LOAD}	**5 pF**	**15 pF**
T	0.93	n/a
E	0.78	n/a
U	0.70	1.48
F or "-": default	0.65	1.30

Table 8. Vdd = 2.5V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)		
Drive Strength \ C_{LOAD}	**5 pF**	**15 pF**
R	1.45	n/a
B	1.09	n/a
T or "-": default	0.62	1.28
E	0.54	1.00
U	0.43	0.96
F	0.34	0.88

Table 9. Vdd = 2.8V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)			
Drive Strength \ C_{LOAD}	**5 pF**	**15 pF**	**30 pF**
R	1.29	n/a	n/a
B	0.97	n/a	n/a
T or "-": default	0.55	1.12	n/a
E	0.44	1.00	n/a
U	0.34	0.88	n/a
F	0.29	0.81	1.48

Table 10. Vdd = 3.0V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)			
Drive Strength \ C_{LOAD}	**5 pF**	**15 pF**	**30 pF**
R	1.22	n/a	n/a
B	0.89	n/a	n/a
T or "-": default	0.51	1.00	n/a
E	0.38	0.92	n/a
U	0.30	0.83	n/a
F	0.27	0.76	1.39

Table 11. Vdd = 3.3V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)			
Drive Strength \ C_{LOAD}	**5 pF**	**15 pF**	**30 pF**
R	1.16	n/a	n/a
B	0.81	n/a	n/a
T or "-": default	0.46	1.00	n/a
E	0.33	0.87	n/a
U	0.28	0.79	1.46
F	0.25	0.72	1.31

Note:

10. "n/a" indicates that the resulting rise/fall time from the respective combination of the drive strength and output load does not provide rail-to-rail swing and is not available.

Pin 1 Configuration Options (OE or NC)

Pin 1 of the SiT8925 can be factory-programmed to support two modes: Output Enable (OE) or No Connect (NC). These modes can also be programmed with the Time Machine II using Field Programmable Oscillators.

Output Enable (OE) Mode

In the OE mode, applying logic low to the OE pin only disables the output driver and puts it in Hi-Z mode. The core of the device continues to operate normally. Power consumption is reduced due to the inactivity of the output. When the OE pin is pulled High, the output is typically enabled in <1µs.

No Connect (NC) Mode

In the NC mode, the device always operates in its normal mode and outputs the specified frequency regardless of the logic level on pin 1.

Table 12 below summarizes the key relevant parameters in the operation of the device in OE or NC mode.

Table 12. OE vs. NC

	OE	NC
Active current 125 MHz (max, 1.8V)	6 mA	6 mA
OE disable current (max. 1.8V)	4 mA	N/A
OE enable time at 110 MHz (max)	130 ns	N/A
Output driver in OE disable	High Z	N/A

Output on Startup and OE Enable

The SiT8925 comes with gated output. Its clock output is accurate to the rated frequency stability within the first pulse from initial device startup.

In addition, the SiT8925 supports “no runt” pulses and “no glitch” output during startup or when the output driver is reenabled from the OE disable mode as shown in the waveform captures in Figure 16 and Figure 17.

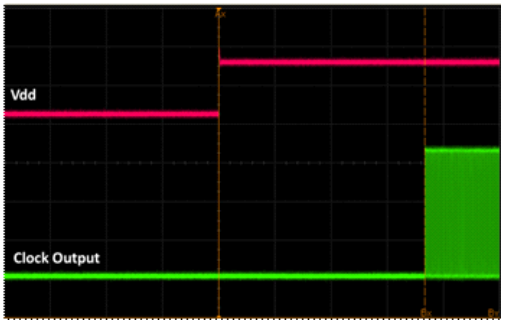


Figure 16. Startup Waveform vs. Vdd

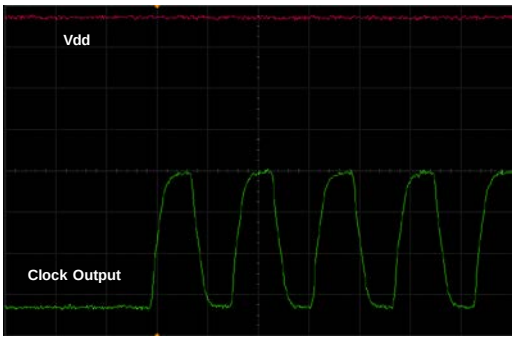
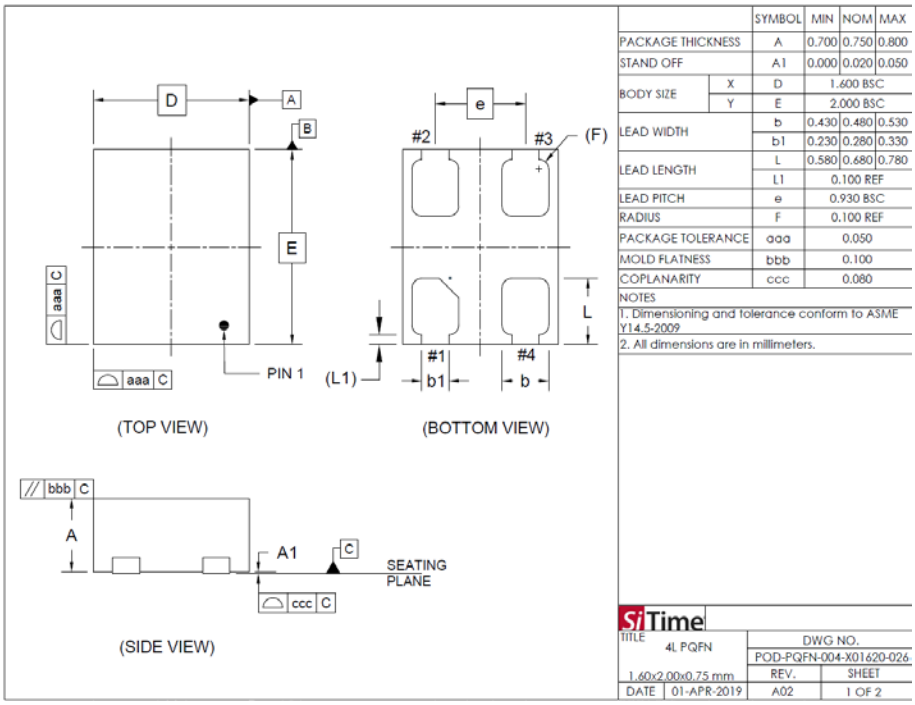


Figure 17. Startup Waveform vs. Vdd (Zoomed-in View of Figure 16)

Dimensions and Patterns

Package Size – Dimensions (Unit: mm)[11]	Recommended Land Pattern (Unit: mm)[12]

2.0 x 1.6 x 0.75 mm

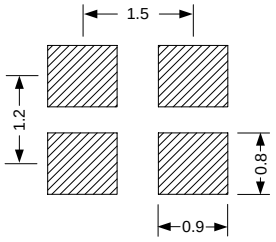


		SYMBOL	MIN	NOM	MAX
PACKAGE THICKNESS		A	0.700	0.750	0.800
STAND OFF		A1	0.000	0.020	0.050
BODY SIZE	X	D		1.600 BSC	
	Y	E		2.000 BSC	
LEAD WIDTH		b	0.430	0.480	0.530
		b1	0.230	0.280	0.330
LEAD LENGTH		L	0.580	0.680	0.780
		L1		0.100 REF	
LEAD PITCH		e		0.930 BSC	
RADIUS		F		0.100 REF	
PACKAGE TOLERANCE		aaa		0.050	
MOLD FLATNESS		bbb		0.100	
COPLANARITY		ccc		0.080	

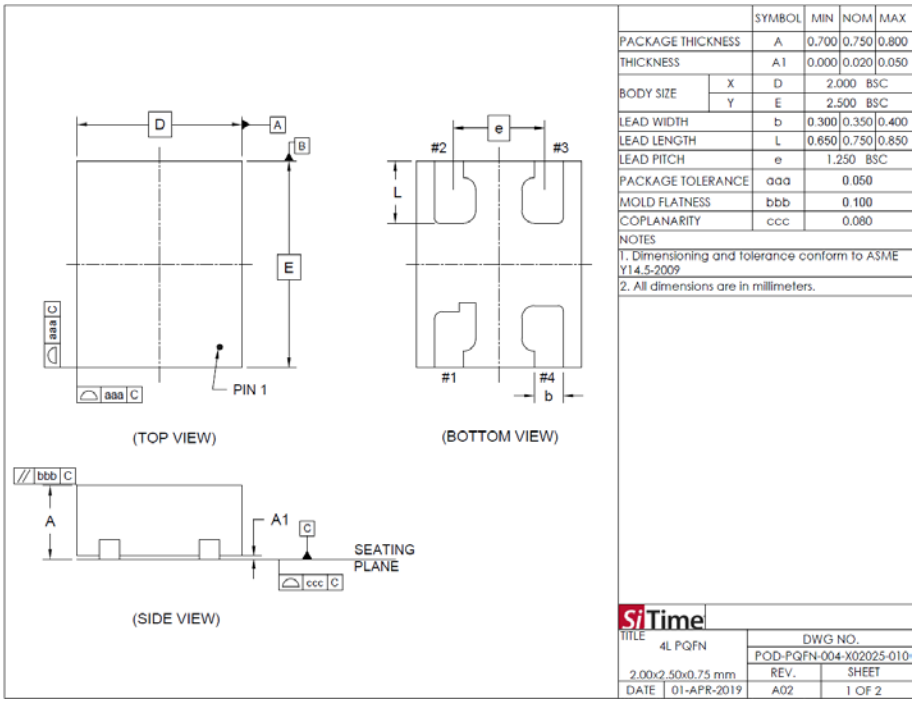
NOTES
1. Dimensioning and tolerance conform to ASME Y14.5-2009
2. All dimensions are in millimeters.

SiTime

TITLE	4L PQFN	DWG NO.	
	1.60x2.00x0.75 mm	REV.	SHEET
DATE	01-APR-2019	A02	1 OF 2



2.5 x 2.0 x 0.75 mm

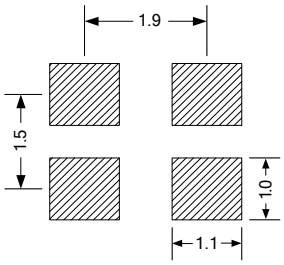


		SYMBOL	MIN	NOM	MAX
PACKAGE THICKNESS		A	0.700	0.750	0.800
THICKNESS		A1	0.000	0.020	0.050
BODY SIZE	X	D		2.000 BSC	
	Y	E		2.500 BSC	
LEAD WIDTH		b	0.300	0.350	0.400
LEAD LENGTH		L	0.650	0.750	0.850
LEAD PITCH		e		1.250 BSC	
PACKAGE TOLERANCE		aaa		0.050	
MOLD FLATNESS		bbb		0.100	
COPLANARITY		ccc		0.080	

NOTES
1. Dimensioning and tolerance conform to ASME Y14.5-2009
2. All dimensions are in millimeters.

SiTime

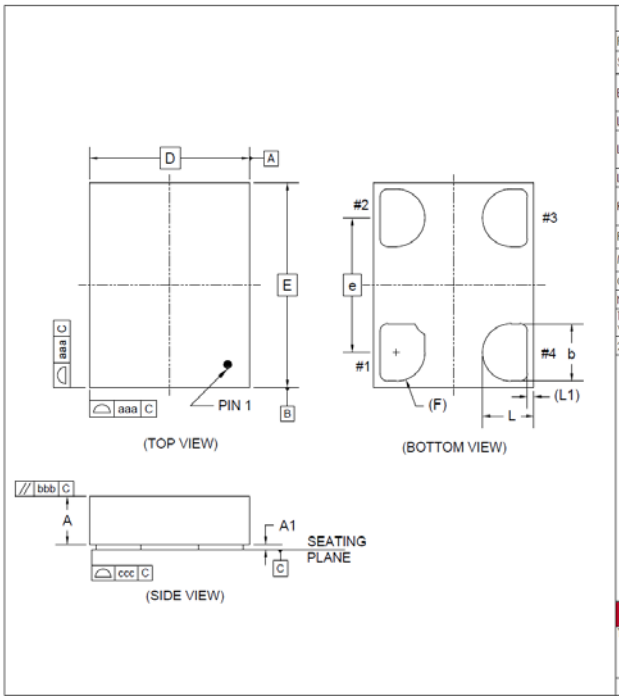
TITLE	4L PQFN	DWG NO.	
	2.00x2.50x0.75 mm	REV.	SHEET
DATE	01-APR-2019	A02	1 OF 2



Dimensions and Patterns (continued)

Package Size – Dimensions (Unit: mm)[11]	Recommended Land Pattern (Unit: mm)[12]

3.2 x 2.5 x 0.75 mm

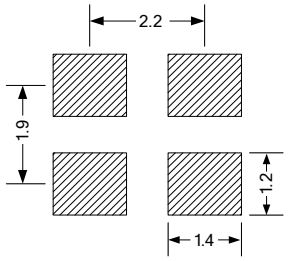


		SYMBOL	MIN	NOM	MAX
PACKAGE THICKNESS		A	0.700	0.750	0.800
STAND OFF		A1	0.000	0.020	0.050
BODY SIZE	X	D		2.500 BSC	
	Y	E		3.200 BSC	
LEAD WIDTH		b	0.800	0.900	1.000
LEAD LENGTH		L	0.700	0.800	0.900
		L1		0.100 REF	
LEAD PITCH		e		2.100 BSC	
RADIUS		F		0.450 REF	
		F1		0.120 REF	
PACKAGE TOLERANCE		aaa		0.050	
MOLD FLATNESS		bbb		0.100	
COPLANARITY		ccc		0.080	

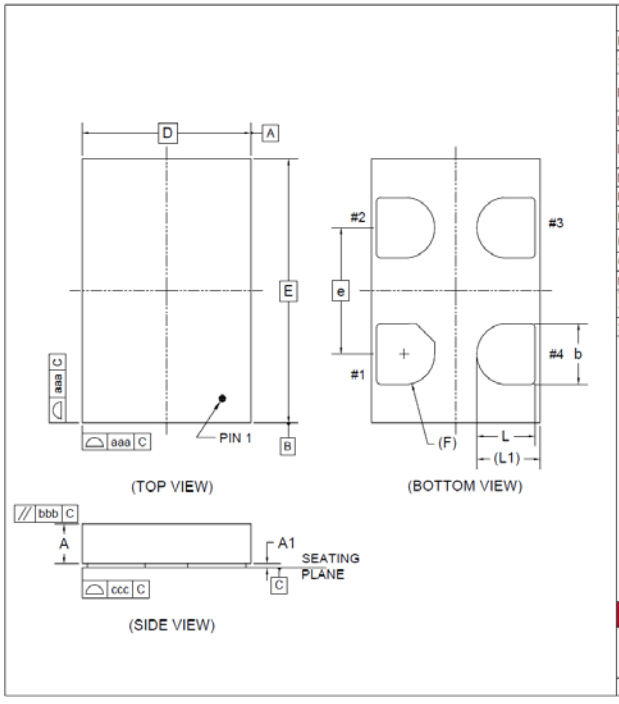
NOTES
1. Dimensioning and tolerance conform to ASME Y14.5-2009
2. All dimensions are in millimeters.

SiTime

TITLE	4L PQFN	DWG NO.	
	3.20x2.50x0.75 mm	POD-PQFN-004-X03225-002	
DATE	01-APR-2019	REV. A04	SHEET 1 OF 2



5.0 x 3.2 x 0.75 mm

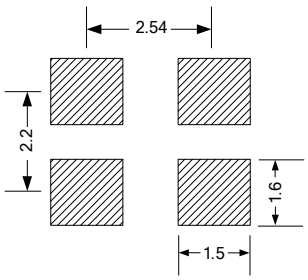


		SYMBOL	MIN	NOM	MAX
PACKAGE THICKNESS		A	0.700	0.750	0.800
STAND OFF		A1	0.000	0.020	0.050
BODY SIZE	X	D		3.200 BSC	
	Y	E		5.000 BSC	
LEAD WIDTH		b	1.000	1.100	1.200
LEAD LENGTH		L	1.050	1.100	1.150
		L1		1.200 REF	
LEAD PITCH		e		2.390 BSC	
RADIUS		F		0.575	
PACKAGE TOLERANCE		aaa		0.050	
MOLD FLATNESS		bbb		0.100	
COPLANARITY		ccc		0.080	

NOTES
1. Dimensioning and tolerance conform to ASME Y14.5-2009
2. All dimensions are in millimeters.

SiTime

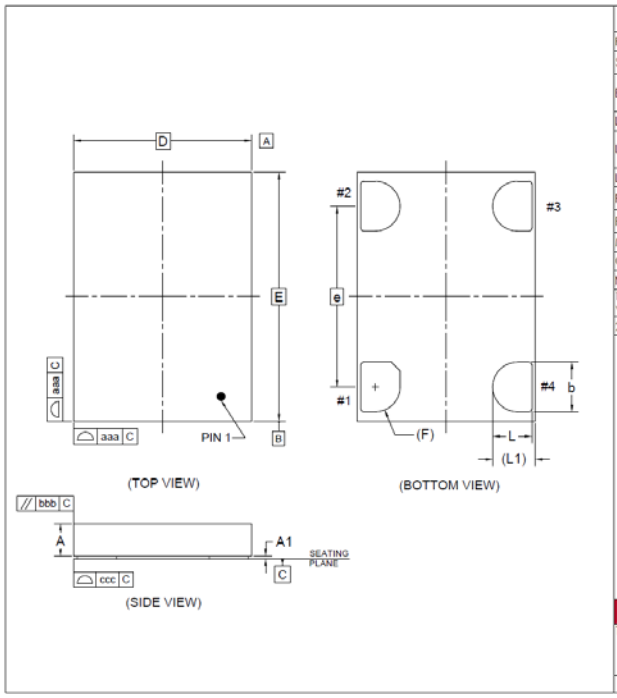
TITLE	4L PQFN	DWG NO.	
	5.00x3.20x0.75 mm	POD-PQFN-004-X05032-003	
DATE	01-APR-2019	REV. A04	SHEET 1 OF 2



Dimensions and Patterns (continued)

Package Size – Dimensions (Unit: mm)[11]	Recommended Land Pattern (Unit: mm)[12]

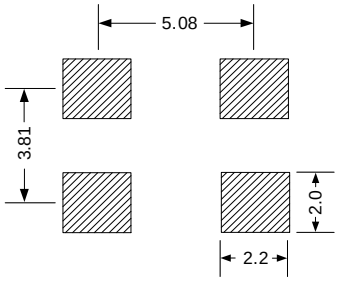
7.0 x 5.0 x 0.90 mm



		SYMBOL	MIN	NOM	MAX
PACKAGE THICKNESS		A	0.800	0.900	1.000
STAND OFF		A1	0.000	0.020	0.050
BODY SIZE	X	D		5.000 BSC	
	Y	E		7.000 BSC	
LEAD WIDTH		b	1.350	1.400	1.450
LEAD LENGTH		L	1.050	1.100	1.150
		L1		1.200 REF	
LEAD PITCH		e		5.080 BSC	
RADIUS		F		0.080 REF	
PACKAGE TOLERANCE		aaa		0.050	
MOLD FLATNESS		bbb		0.100	
COPLANARITY		ccc		0.080	

NOTES
1. Dimensioning and tolerance conform to ASME Y14.5-2009
2. All dimensions are in millimeters.

SiTime			
TITLE	4L PQFN	DWG NO.	POD-PQFN-004-X07050-011
	7.00x5.00x0.90 mm	REV.	SHEET
DATE	01-APR-2019	A02	1 OF 2

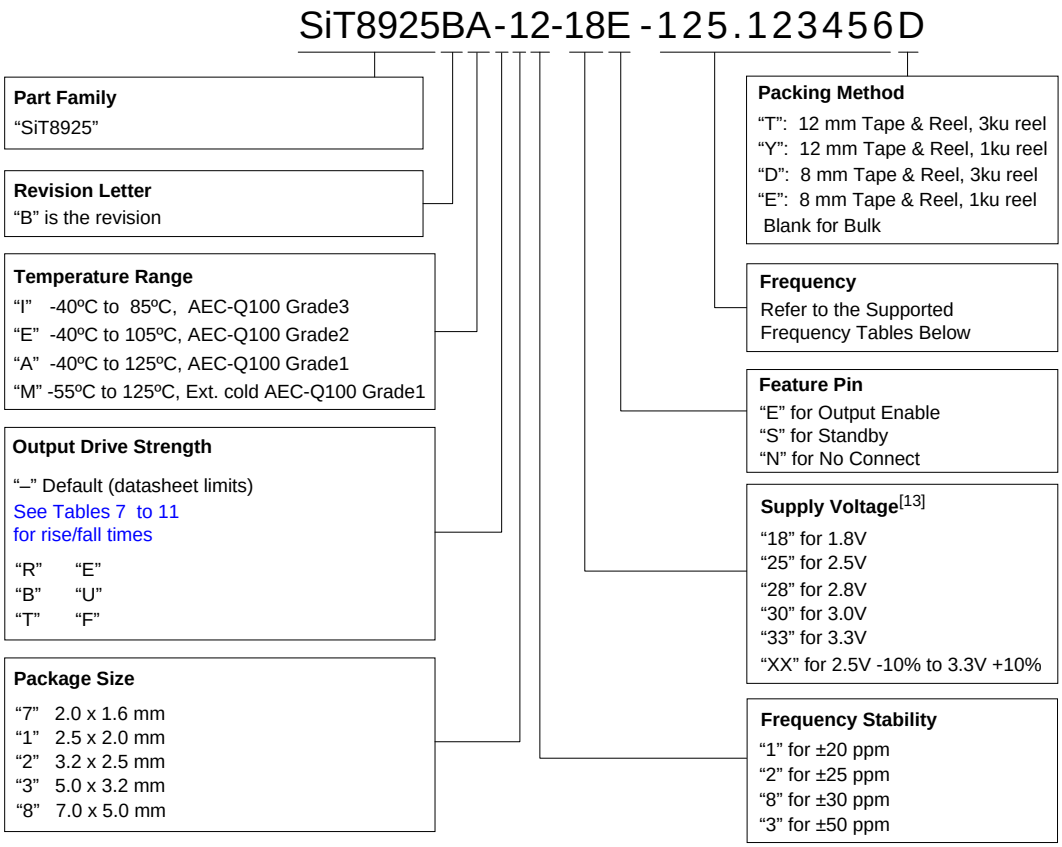


Notes:

11. Top marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device.
12. A capacitor of value 0.1 µF or higher between Vdd and GND is required.

Ordering Information

The following part number guide is for reference only. To customize and build an exact part number, use the SiTime Part Number Generator.



Note:

13. The voltage portion of the SiT8925 part number consists of two characters that denote the specific supply voltage of the device. The SiT8925 supports either 1.8V ±10% or any voltage between 2.25V and 3.63V. In the 1.8V mode, one can simply insert 18 in the part number. In the 2.5V to 3.3V mode, two digits such as 18, 25 or 33 can be used in the part number to reflect the desired voltage. Alternatively, "XX" can be used to indicate the entire operating voltage range from 2.25V to 3.63V.

Table 13. Supported Frequencies (-40°C to +85°C) [14]

Frequency Range	
Min.	Max.
115.200000 MHz	137.000000 MHz

Table 14. Supported Frequencies (-40°C to +105°C or -40°C to +125°C) [14, 15]

Frequency Range	
Min.	Max.
115.194001 MHz	117.810999 MHz
118.038001 MHz	118.593999 MHz
118.743001 MHz	122.141999 MHz
122.705001 MHz	123.021999 MHz
123.348001 MHz	137.000000 MHz

Table 15. Supported Frequencies (-55°C to +125°C) [14, 15]

Frequency Range	
Min.	Max.
119.342001 MHz	120.238999 MHz
120.262001 MHz	121.169999 MHz
121.243001 MHz	121.600999 MHz
123.948001 MHz	137.000000 MHz

Notes:

14. Any frequency within the min and max values in the above tables are supported with 6 decimal places of accuracy.
15. Please contact SiTime for frequencies that are not listed in the tables above.

Table 16. Ordering Codes for Supported Tape & Reel Packing Method

Device Size	16 mm T&R (3ku)	16 mm T&R (1ku)	12 mm T&R (3ku)	12 mm T&R (1ku)	8 mm T&R (3ku)	8 mm T&R (1ku)
2.0 x 1.6 mm	–	–	–	–	D	E
2.5 x 2.0 mm	–	–	–	–	D	E
3.2 x 2.5 mm	–	–	–	–	D	E
5.0 x 3.2 mm	–	–	T	Y	–	–
7.0 x 5.0 mm	T	Y	–	–	–	–

Table 17. Additional Information

Document	Description	Download Link
Time Machine II	MEMS oscillator programmer	http://www.sitime.com/support/time-machine-oscillator-programmer
Field Programmable Oscillators	Devices that can be programmable in the field by Time Machine II	http://www.sitime.com/products/field-programmable-oscillators
Manufacturing Notes	Tape & Reel dimension, reflow profile and other manufacturing related info	http://www.sitime.com/manufacturing-notes
Qualification Reports	RoHS report, reliability reports, composition reports	http://www.sitime.com/support/quality-and-reliability
Performance Reports	Additional performance data such as phase noise, current consumption and jitter for selected frequencies	http://www.sitime.com/support/performance-measurement-report
Termination Techniques	Termination design recommendations	http://www.sitime.com/support/application-notes
Layout Techniques	Layout recommendations	http://www.sitime.com/support/application-notes

Table 18. Revision History

Revision	Release Date	Change Summary
0.1	05/28/2015	Final production release
1.3	03/18/2016	Added the industrial temperature "-40°C to ±85°C" option Added support for ±20 ppm frequency stability Added 12 and 16 mm T&R information to Table 16
1.5	02/16/2018	Changed Clock Generator to SOT23 Oscillator
1.6	07/18/2018	Added Standby mode option Removed center lines from the package drawings Revised description of temperature range options Updated logo and company address, links and other page layout changes
1.7	05/22/2019	Updated package dimensions Revised startup time specification

SiTime Corporation, 5451 Patrick Henry Drive, Santa Clara, CA 95054, USA | **Phone:** +1-408-328-4400 | **Fax:** +1-408-328-4439

© SiTime Corporation 2015-2019. The information contained herein is subject to change at any time without notice. SiTime assumes no responsibility or liability for any loss, damage or defect of a Product which is caused in whole or in part by (i) use of any circuitry other than circuitry embodied in a SiTime product, (ii) misuse or abuse including static discharge, neglect or accident, (iii) unauthorized modification or repairs which have been soldered or altered during assembly and are not capable of being tested by SiTime under its normal test conditions, or (iv) improper installation, storage, handling, warehousing or transportation, or (v) being subjected to unusual physical, thermal, or electrical stress.

Disclaimer: SiTime makes no warranty of any kind, express or implied, with regard to this material, and specifically disclaims any and all express or implied warranties, either in fact or by operation of law, statutory or otherwise, including the implied warranties of merchantability and fitness for use or a particular purpose, and any implied warranty arising from course of dealing or usage of trade, as well as any common-law duties relating to accuracy or lack of negligence, with respect to this material, any SiTime product and any product documentation. Products sold by SiTime are not suitable or intended to be used in a life support application or component, to operate nuclear facilities, or in other mission critical applications where human life may be involved or at stake. All sales are made conditioned upon compliance with the critical uses policy set forth below.

CRITICAL USE EXCLUSION POLICY
BUYER AGREES NOT TO USE SITIME'S PRODUCTS FOR ANY APPLICATION OR IN ANY COMPONENTS USED IN LIFE SUPPORT DEVICES OR TO OPERATE NUCLEAR FACILITIES OR FOR USE IN OTHER MISSION-CRITICAL APPLICATIONS OR COMPONENTS WHERE HUMAN LIFE OR PROPERTY MAY BE AT STAKE.

SiTime owns all rights, title and interest to the intellectual property related to SiTime's products, including any software, firmware, copyright, patent, or trademark. The sale of SiTime products does not convey or imply any license under patent or other rights. SiTime retains the copyright and trademark rights in all documents, catalogs and plans supplied pursuant to or ancillary to the sale of products or services by SiTime. Unless otherwise agreed to in writing by SiTime, any reproduction, modification, translation, compilation, or representation of this material shall be strictly prohibited.

Supplemental Information

The Supplemental Information section is not part of the datasheet and is for informational purposes only.

Best Reliability

Silicon is inherently more reliable than quartz. Unlike quartz suppliers, SiTime has in-house MEMS and analog CMOS expertise, which allows SiTime to develop the most reliable products. Figure 1 shows a comparison with quartz technology.

Why is SiTime Best in Class:

- SiTime's MEMS resonators are vacuum sealed using an advanced EpiSeal™ process, which eliminates foreign particles and improves long term aging and reliability
- World-class MEMS and CMOS design expertise

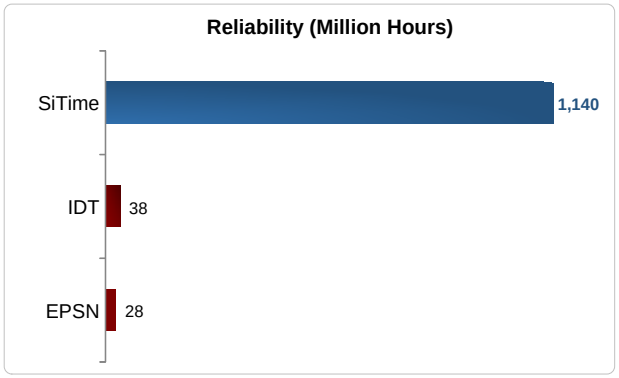


Figure 1. Reliability Comparison[1]

Best Aging

Unlike quartz, MEMS oscillators have excellent long term aging performance which is why every new SiTime product specifies 10-year aging. A comparison is shown in Figure 2.

Why is SiTime Best in Class:

- SiTime's MEMS resonators are vacuum sealed using an advanced EpiSeal™ process, which eliminates foreign particles and improves long term aging and reliability
- Inherently better immunity of electrostatically driven MEMS resonator

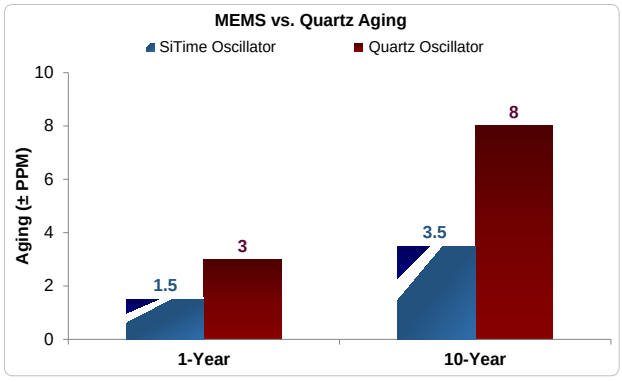


Figure 2. Aging Comparison[2]

Best Electro Magnetic Susceptibility (EMS)

SiTime's oscillators in plastic packages are up to 54 times more immune to external electromagnetic fields than quartz oscillators as shown in Figure 3.

Why is SiTime Best in Class:

- Internal differential architecture for best common mode noise rejection
- Electrostatically driven MEMS resonator is more immune to EMS

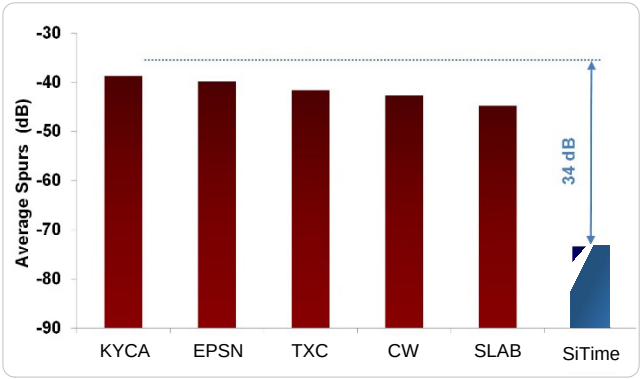


Figure 3. Electro Magnetic Susceptibility (EMS)[3]

Best Power Supply Noise Rejection

SiTime's MEMS oscillators are more resilient against noise on the power supply. A comparison is shown in Figure 4.

Why is SiTime Best in Class:

- On-chip regulators and internal differential architecture for common mode noise rejection
- MEMS resonator is paired with advanced analog CMOS IC

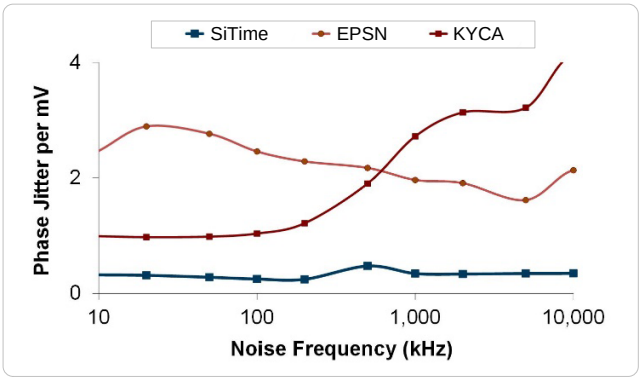


Figure 4. Power Supply Noise Rejection[4]

Best Vibration Robustness

High-vibration environments are all around us. All electronics, from handheld devices to enterprise servers and storage systems are subject to vibration. Figure 5 shows a comparison of vibration robustness.

Why is SiTime Best in Class:

- The moving mass of SiTime's MEMS resonators is up to 3000 times smaller than quartz
- Center-anchored MEMS resonator is the most robust design

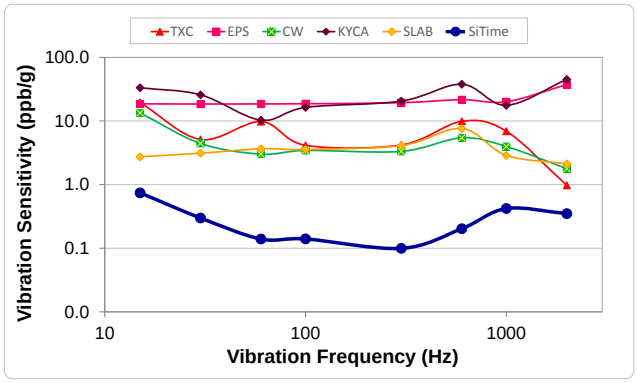


Figure 5. Vibration Robustness[5]

Figure labels:

- TXC = TXC
- Epson = EPSN
- Connor Winfield = CW
- Kyocera = KYCA
- SiLabs = SLAB
- SiTime = EpiSeal MEMS

Best Shock Robustness

SiTime's oscillators can withstand at least 50,000 g shock. They all maintain their electrical performance in operation during shock events. A comparison with quartz devices is shown in Figure 6.

Why is SiTime Best in Class:

- The moving mass of SiTime's MEMS resonators is up to 3000 times smaller than quartz
- Center-anchored MEMS resonator is the most robust design

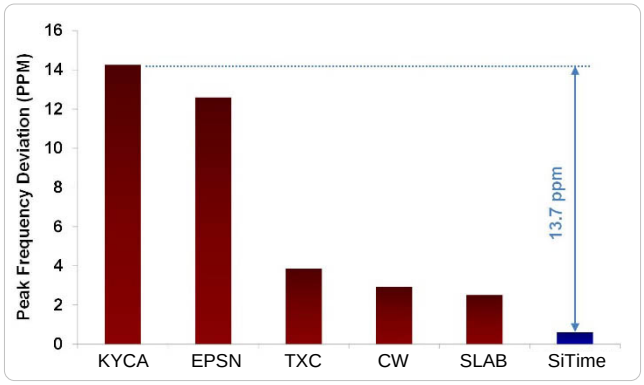


Figure 6. Shock Robustness[6]

Notes:

1. Data source: Reliability documents of named companies.
2. Data source: SiTime and quartz oscillator devices datasheets.
3. Test conditions for Electro Magnetic Susceptibility (EMS):
   - According to IEC EN61000-4.3 (Electromagnetic compatibility standard)
   - Field strength: 3V/m
   - Radiated signal modulation: AM 1 kHz at 80% depth
   - Carrier frequency scan: 80 MHz – 1 GHz in 1% steps
   - Antenna polarization: Vertical
   - DUT position: Center aligned to antenna

   Devices used in this test:

Label	Manufacturer	Part Number	Technology
EpiSeal MEMS	SiTime	SiT9120AC-1D2-33E156.250000	MEMS + PLL
EPSN	Epson	EG-2102CA156.2500M-PHPAL3	Quartz, SAW
TXC	TXC	BB-156.250MBE-T	Quartz, 3rd Overtone
CW	Conner Winfield	P123-156.25M	Quartz, 3rd Overtone
KYCA	AVX Kyocera	KC7050T156.250P30E00	Quartz, SAW
SLAB	SiLab	590AB-BDG	Quartz, 3rd Overtone + PLL

4. 50 mV pk-pk Sinusoidal voltage.

   Devices used in this test:

Label	Manufacturer	Part Number	Technology
EpiSeal MEMS	SiTime	SiT8208AI-33-33E-25.000000	MEMS + PLL
NDK	NDK	NZ2523SB-25.6M	Quartz
KYCA	AVX Kyocera	KC2016B25M0C1GE00	Quartz
EPSN	Epson	SG-310SCF-25M0-MB3	Quartz

5. Devices used in this test:
   same as EMS test stated in Note 3.
6. Test conditions for shock test:
   - MIL-STD-883F Method 2002
   - Condition A: half sine wave shock pulse, 500-g, 1ms
   - Continuous frequency measurement in 100 µs gate time for 10 seconds

   Devices used in this test:
   same as EMS test stated in Note 3.
7. Additional data, including setup and detailed results, is available upon request to qualified customer. Please contact productsupport@sitime.com.